

### General Description

The WSD65N12GDN56 is SGT II technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

The WSD65N12GDN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

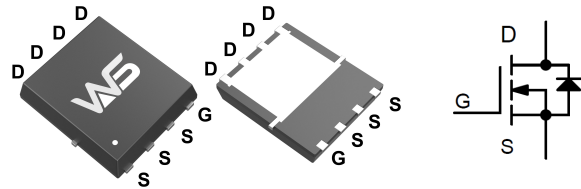
### Product Summary

BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
120V	10mΩ	72A

### Applications

- Mobile phone fast charging.
- Brushless motor
- Home appliance control board

### DFN5X6 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	120	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D@T<sub>C</sub>=25°C</sub>	Continuous Drain Current	72	A
I <sub>DP</sub>	Pulsed Drain Current	150	A
EAS	Avalanche Energy, Single pulse	50	mJ
P <sub>D@T<sub>C</sub>=25°C</sub>	Total Power Dissipation	140	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	25	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	0.89	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

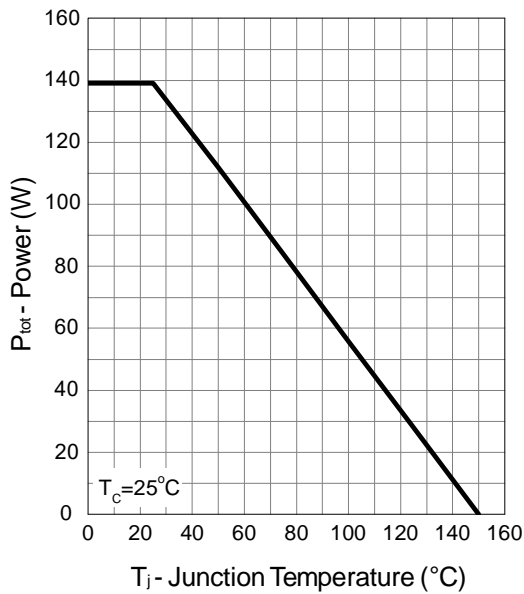
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	120	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =10A.	---	10	12	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A.	---	15	23	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	2.0	3.0	4.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =25A	---	33	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	5.6	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	7.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =2Ω, I <sub>D</sub> =25A	---	22	---	ns
T <sub>r</sub>	Rise Time		---	10	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	85	---	
T <sub>f</sub>	Fall Time		---	112	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	---	2640	---	pF
C <sub>oss</sub>	Output Capacitance		---	330	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	11	---	
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	50	A
I <sub>SP</sub>	Pulsed Source Current		---	---	150	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =12A, T <sub>J</sub> =25°C	---	---	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =25A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	62	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	135	---	nC

**Note**

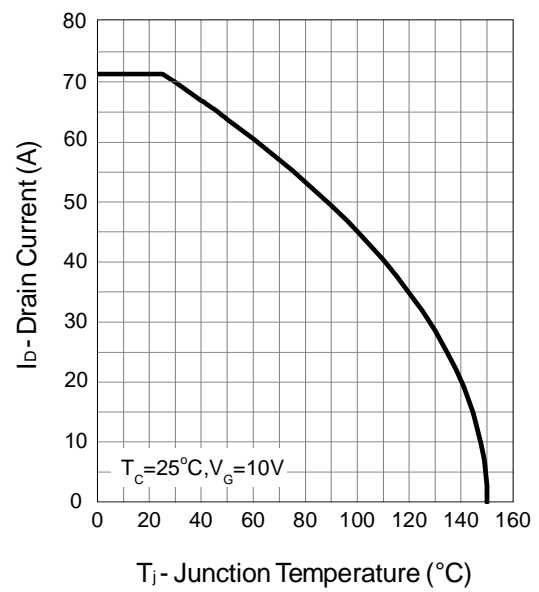
- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of R<sub>θJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25 °C.
- 5) V<sub>DD</sub>=50 V, R<sub>G</sub>=25 Ω, L=0.3 mH, starting T<sub>J</sub>=25 °C.

**Typical Operating Characteristics**

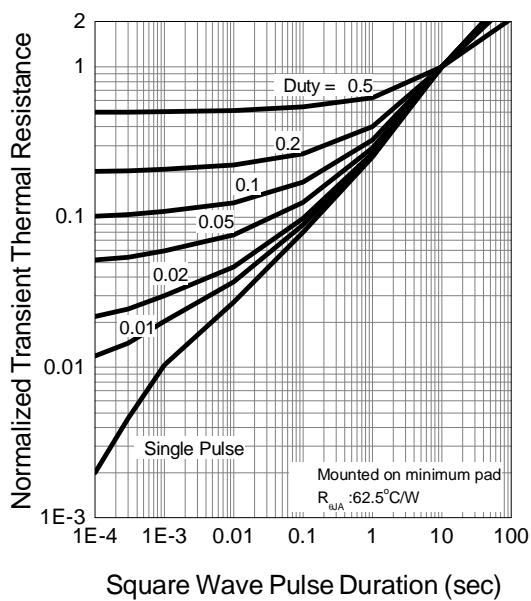
**Power Dissipation**



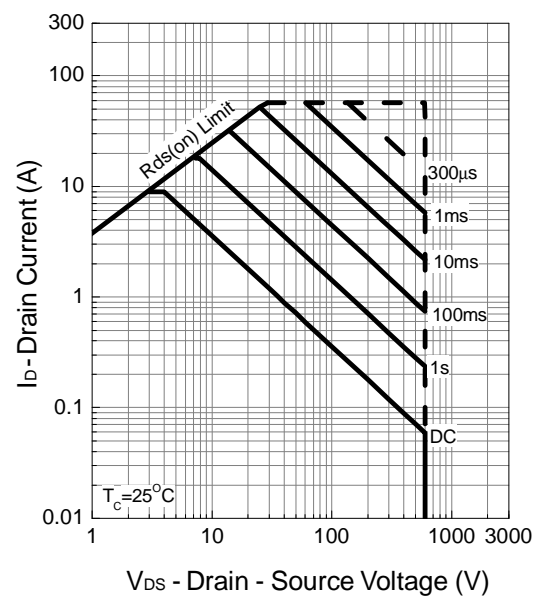
**Drain Current**



**Thermal Transient Impedance:**

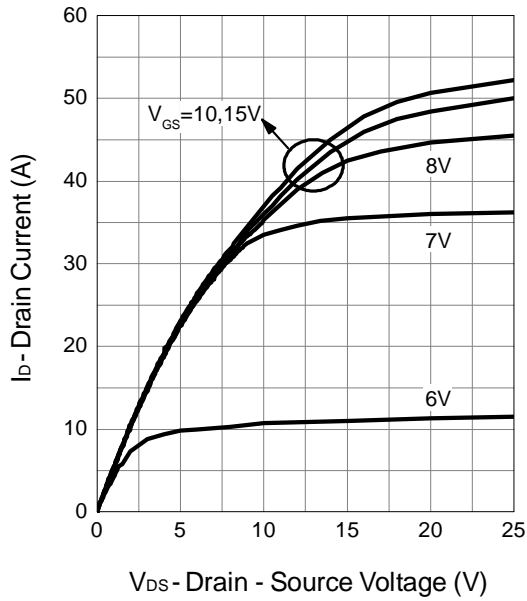


**Safe Operation Area**

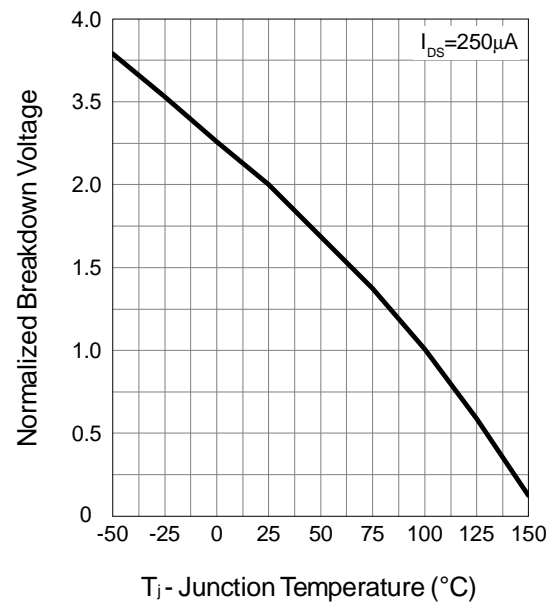


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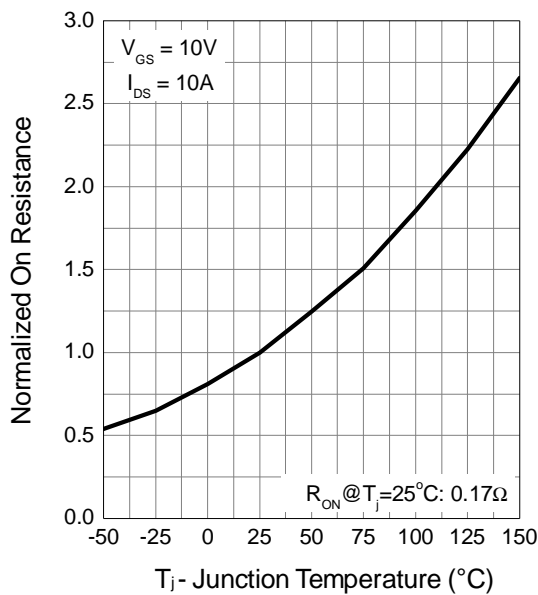
**Output Characteristics**



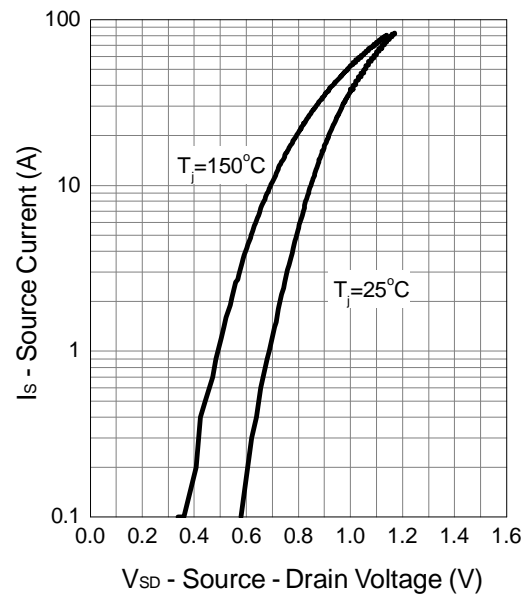
**$V_{GS(th)}$  vs Junction Temperature**



**Drain-Source On Resistance**

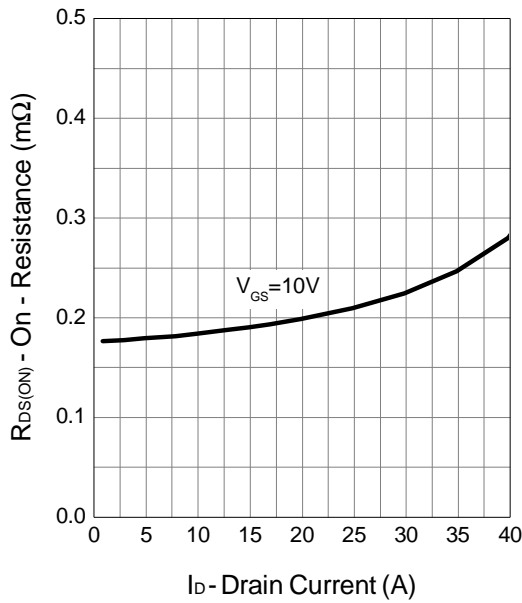


**Source-Drain Diode Forward**

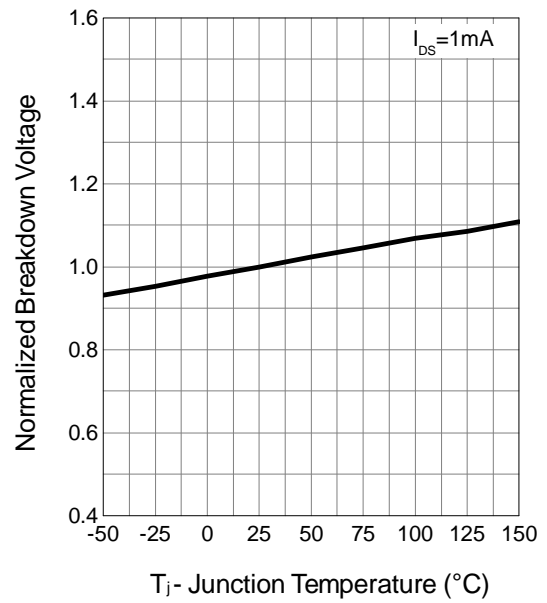


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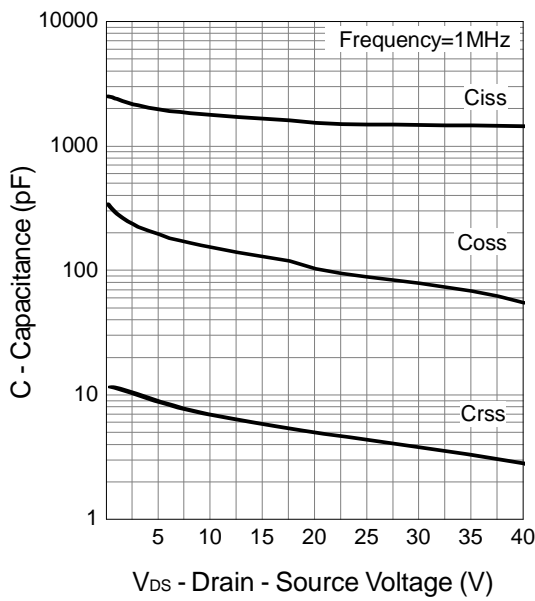
**Drain-Source On Resistance**



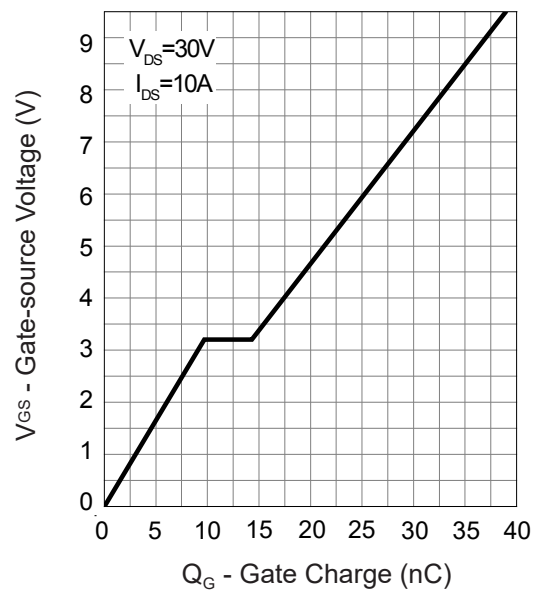
**BVDSS vs Junction Temperature**



**Capacitance**



**Gate Charge**





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